Di Wu

List of Publications by Year
in descending order

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195	6,213	94269	82410
papers	citations	37 h-index	72 g-index

195	195	195	8274
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Magnetic properties of multiferroic Pb5Fe3F19. Journal of Magnetism and Magnetic Materials, 2022, 541, 168540.	1.0	2
2	The magnetic properties of multiferroic Ba5Fe3F19â˜Î´. Journal of Magnetism and Magnetic Materials, 2022, 541, 168541.	1.0	2
3	Flexoelectric-induced photovoltaic effects and tunable photocurrents in flexible LaFeO3 epitaxial heterostructures. Journal of Materiomics, 2022, 8, 281-287.	2.8	7
4	Giant Thermal Transport Tuning at a Metal/Ferroelectric Interface. Advanced Materials, 2022, 34, e2105778.	11.1	13
5	Dualâ€Design of Nanoporous to Compact Interface via Atomic/Molecular Layer Deposition Enabling a Longâ€Life Silicon Anode. Advanced Functional Materials, 2022, 32, 2109682.	7.8	26
6	Stable pH sensitivity of LaAlO3/SrTiO3 interfacial electronic gas. Current Applied Physics, 2022, 34, 55-58.	1.1	4
7	Magnetic phase transition induced ferroelectric polarization in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BaFeF</mml:mi><mml:mn>4</mml:mn></mml:msub> with room-temperature weak ferromagnetism. Physical Review Materials, 2022, 6, .	3.1	1
8	Transition of laser-induced terahertz spin currents from torque- to conduction-electron-mediated transport. Physical Review B, 2022, 105, .	1.1	17
9	Anisotropic magnetostructural transition in epitaxial Mnâ€“Niâ€“Coâ€“Ti Heusler alloy thin film. Journal of Applied Physics, 2022, 131, 173902.	1.1	2
10	Thickness-dependent structural phase transition and self-intercalation of two-dimensional ferromagnetic chromium telluride thin films. Applied Physics Letters, 2022, 120, 261602.	1.5	3
11	Perpendicular Magnetic Anisotropic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Ni</mml:mi><mml:mi>Co</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub> mathvariant="normal">O</mml:mi></mml:mrow></mml:mrow><mml:mn>4</mml:mn></mml:msub></mml:math> Epitaxial Films with Tunable Coercivity. Physical Review Applied, 2022, 18, .	4.3	6
12	Ultrafast spin current generated from an antiferromagnet. Nature Physics, 2021, 17, 388-394.	6.5	81
13	Spinâ€“orbit torque and Dzyaloshinskiiâ€“Moriya interaction in perpendicularly magnetized heterostructures with iridium. Applied Physics Letters, 2021, 118, 062409.	1.5	5
14	Electrically tunable inverse spin Hall effect in SrIrO3/Pb(Mg1/3Nb2/3)0.7 Ti0.3O3 heterostructures through interface strain coupling. Applied Physics Letters, 2021, 118, .	1.5	4
15	Band structure engineering of van der Waals heterostructures using ferroelectric clamped sandwich structures. Physical Review B, 2021, 103, .	1.1	11
16	Strain Control of Phase Transition and Exchange Bias in Flexible Heusler Alloy Thin Films. ACS Applied Materials & Interfaces, 2021, 13, 24285-24294.	4.0	12
17	Tailoring Stress and Ion-Transport Kinetics via a Molecular Layer Deposition-Induced Artificial Solid Electrolyte Interphase for Durable Silicon Composite Anodes. ACS Applied Materials & Interfaces, 2021, 13, 32520-32530.	4.0	16
18	Electroresistance in metal/ferroelectric/semiconductor tunnel junctions based on a Hf0.5Zr0.5O2 barrier. Applied Physics Letters, 2021, 118, .	1.5	14

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19	Atomic-scale fatigue mechanism of ferroelectric tunnel junctions. Science Advances, 2021, 7, eabh2716.	4.7	25
20	Polymerized hybrid Hf-based hydroquinone/Al₂O₃ bilayer structure by molecular/atomic layer deposition for non-volatile resistive random access memory. APL Materials, 2021, 9, 121110.	2.2	6
21	Ferroelectric Tunnel Junctions: Modulations on the Potential Barrier. Advanced Materials, 2020, 32, e1904123.	11.1	179
22	Synaptic functions and a memristive mechanism on Pt/AlO_x/HfO_x/TiN bilayer-structure memristors. Journal Physics D: Applied Physics, 2020, 53, 035302.	1.3	20
23	Light-Enhanced Spin Diffusion in Hybrid Perovskite Thin Films and Single Crystals. ACS Applied Materials & Interfaces, 2020, 12, 3205-3213.	4.0	17
24	Simulation of Biologic Synapse Through Organic-Inorganic Hybrid Memristors Using Novel Ti-Based Maleic Acid/TiO2 Ultrathin Films. IEEE Electron Device Letters, 2020, 41, 155-158.	2.2	14
25	Experimental Observation of the Gate-Controlled Reversal of the Anomalous Hall Effect in the Intrinsic Magnetic Topological Insulator MnBi₂Te₄ Device. Nano Letters, 2020, 20, 709-714.	4.5	60
26	Titanicone-derived TiO₂ quantum dot@carbon encapsulated ZnO nanorod anodes for stable lithium storage. Dalton Transactions, 2020, 49, 10866-10873.	1.6	9
27	One-step facile preparation of zinc-based hydroquinone hybrid nanoporous thin films by molecular layer deposition. Applied Physics Letters, 2020, 117, 031601.	1.5	9
28	Optimization of oxygen vacancy concentration in HfO2/HfOx bilayer-structured ultrathin memristors by atomic layer deposition and their biological synaptic behavior. Journal of Materials Chemistry C, 2020, 8, 12478-12484.	2.7	22
29	Spin-Filtering Ferroelectric Tunnel Junctions as Multiferroic Synapses for Neuromorphic Computing. ACS Applied Materials & Interfaces, 2020, 12, 56300-56309.	4.0	37
30	Conductivity Modulation of a Slit Channel in a Monolayer MoS 2 Homostructure. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000082.	1.2	0
31	Preparation and characterization of a flexible ferroelectric tunnel junction. Applied Physics Letters, 2020, 116, .	1.5	14
32	Ferroelasticâ€Domainâ€Assisted Mechanical Switching of Ferroelectric Domains in Pb(Zr,Ti)O₃ Thin Films. Advanced Electronic Materials, 2020, 6, 2000300.	2.6	12
33	Atomic layer deposition of ZnO/TiO2 nanolaminates as ultra-long life anode material for lithium-ion batteries. Scientific Reports, 2019, 9, 11526.	1.6	38
34	Interface electron transfer and thickness dependent transport characteristics of La_{0.7}Sr_{0.3}VO₃thin films. Journal of Physics Condensed Matter, 2019, 31, 245002.	0.7	0
35	Comparison of chemical stability and corrosion resistance of group IV metal oxide films formed by thermal and plasma-enhanced atomic layer deposition. Scientific Reports, 2019, 9, 10438.	1.6	30
36	Evaluation of the Structural Phase Transition in Multiferroic (Bi1â^'x Prx)(Fe0.95 Mn0.05)O3 Thin Films by A Multi-Technique Approach Including Picosecond Laser Ultrasonics. Applied Sciences (Switzerland), 2019, 9, 736.	1.3	3

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37	Freestanding crystalline oxide perovskites down to the monolayer limit. Nature, 2019, 570, 87-90.	13.7	398
38	Imaging quantum spin Hall edges in monolayer WTe ₂. Science Advances, 2019, 5, eaat8799.	4.7	113
39	Biomimetic strain sensors based on patterned polydimethylsiloxane and Ir nanoparticles decorated multi-walled carbon nanotubes. Sensors and Actuators A: Physical, 2019, 289, 57-64.	2.0	19
40	Growth Mechanism, Ambient Stability, and Charge Trapping Ability of Ti-Based Maleic Acid Hybrid Films by Molecular Layer Deposition. Langmuir, 2019, 35, 3020-3030.	1.6	10
41	Metalâ€“Insulator Transition of LaNiO₃ Films in LaNiO₃/SrIrO₃ Heterostructures. ACS Applied Materials & Interfaces, 2019, 11, 3565-3570.	4.0	6
42	Outstanding memory characteristics with atomic layer deposited Ta2O5/Al2O3/TiO2/Al2O3/Ta2O5 nanocomposite structures as the charge trapping layer. Applied Surface Science, 2019, 467-468, 423-427.	3.1	12
43	Observation of spin-orbit magnetoresistance in metallic thin films on magnetic insulators. Science Advances, 2018, 4, eaao3318.	4.7	32
44	Spin Injection and Transport in Organic Spin Valves. Materials and Energy, 2018, , 93-129.	2.5	1
45	A comparative study of growth and properties of atomic layer deposited transparent conductive oxide of Al doped ZnO films from different Al precursors. Thin Solid Films, 2018, 646, 126-131.	0.8	24
46	Self-consistent determination of spin Hall angle and spin diffusion length in Pt and Pd: The role of the interface spin loss. Science Advances, 2018, 4, eaat1670.	4.7	157
47	TiOxNy Modified TiO2 Powders Prepared by Plasma Enhanced Atomic Layer Deposition for Highly Visible Light Photocatalysis. Scientific Reports, 2018, 8, 12131.	1.6	21
48	Synaptic Plasticity and Learning Behaviors Mimicked in Single Inorganic Synapses of Pt/HfOx/ZnOx/TiN Memristive System. Nanoscale Research Letters, 2017, 12, 65.	3.1	46
49	Electroelastic Greenâ€™s function of one-dimensional piezoelectric quasicrystals subjected to multi-physics loads. Journal of Intelligent Material Systems and Structures, 2017, 28, 1651-1661.	1.4	19
50	Atomic Layer Deposited Oxide-Based Nanocomposite Structures with Embedded CoPt_x Nanocrystals for Resistive Random Access Memory Applications. ACS Applied Materials & Interfaces, 2017, 9, 6634-6643.	4.0	33
51	A high-throughput stereo-imaging system for quantifying rape leaf traits during the seedling stage. Plant Methods, 2017, 13, 7.	1.9	59
52	High-resolution characterization of multiferroic heterojunction using aberration-corrected scanning transmission electron microscopy. Applied Physics Letters, 2017, 110, .	1.5	10
53	Giant tunnelling electroresistance in metal/ferroelectric/semiconductor tunnel junctions by engineering the Schottky barrier. Nature Communications, 2017, 8, 15217.	5.8	165
54	Out-of-Plane Piezoelectricity and Ferroelectricity in Layered Î±-In₂Se₃ Nanoflakes. Nano Letters, 2017, 17, 5508-5513.	4.5	567

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55	ZnO/ZnS Core-Shell Nanowires Arrays on Ni Foam Prepared by Atomic Layer Deposition for High Performance Supercapacitors. Journal of the Electrochemical Society, 2017, 164, A3493-A3498.	1.3	21
56	Atomic-Layer-Deposition Assisted Formation of Wafer-Scale Double-Layer Metal Nanoparticles with Tunable Nanogap for Surface-Enhanced Raman Scattering. Scientific Reports, 2017, 7, 5161.	1.6	18
57	Interfacial, Electrical, and Band Alignment Characteristics of HfO2/Ge Stacks with In Situ-Formed SiO2 Interlayer by Plasma-Enhanced Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 370.	3.1	8
58	Bipolar Resistive Switching Characteristics of HfO2/TiO2/HfO2 Trilayer-Structure RRAM Devices on Pt and TiN-Coated Substrates Fabricated by Atomic Layer Deposition. Nanoscale Research Letters, 2017, 12, 393.	3.1	64
59	Controlling the assembly and spin transport of tetrathiafulvalene carboxylate coated iron oxide nanoparticles. Journal of Materials Chemistry C, 2017, 5, 7200-7206.	2.7	5
60	Chemical strain-dependent two-dimensional transport at <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>R</mml:mi><mml:msub><mml:mtext>AlO</mml:mtext><mml:mtext><</mml:mtext> interfaces <mml:math		

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73	Improved thermal stability and electrical properties of atomic layer deposited HfO2/AlN high-k gate dielectric stacks on GaAs. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	4
74	Interface modulation and resistive switching evolution in Pt/NiO x /Al2O3/n+â€“Si structure. Applied Physics A: Materials Science and Processing, 2015, 118, 1365-1370.	1.1	2
75	Growth characteristics of Ti-based fumaric acid hybrid thin films by molecular layer deposition. Dalton Transactions, 2015, 44, 14782-14792.	1.6	24
76	Electromechanical Response from LaAlO₃/SrTiO₃ Heterostructures. ACS Applied Materials & Interfaces, 2015, 7, 10146-10151.	4.0	13
77	Stepwise mechanism and H2O-assisted hydrolysis in atomic layer deposition of SiO2 without a catalyst. Nanoscale Research Letters, 2015, 10, 68.	3.1	10
78	Excellent resistive switching properties of atomic layer-deposited Al2O3/HfO2/Al2O3 trilayer structures for non-volatile memory applications. Nanoscale Research Letters, 2015, 10, 135.	3.1	84
79	Thickness-dependent metal-insulator transition in epitaxial SrRuO3 ultrathin films. Journal of Applied Physics, 2015, 117, .	1.1	54
80	Interfacial structure in epitaxial perovskite oxides on (001) Ge crystal. Applied Physics Letters, 2015, 106, .	1.5	11
81	Thickness-Dependent Dielectric Constant of Few-Layer In₂Se₃ Nanoflakes. Nano Letters, 2015, 15, 8136-8140.	4.5	99
82	Photocatalytic activity and photocorrosion of atomic layer deposited ZnO ultrathin films for the degradation of methylene blue. Nanotechnology, 2015, 26, 024002.	1.3	40
83	Interfacial dislocations in (111) oriented (Ba0.7Sr0.3)TiO3films on SrTiO3single crystal. Applied Physics Letters, 2015, 107, 141605.	1.5	2
84	Resistive switching of Pt/ZrO2/YBa2Cu3O7sandwiches. EPJ Applied Physics, 2014, 65, 31303.	0.3	0
85	Growth of high-density Ir nanocrystals by atomic layer deposition for nonvolatile nanocrystal memory applications. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 042201.	0.6	5
86	Anomalous Hall effect in Co/Ni multilayers with perpendicular magnetic anisotropy. Applied Physics Letters, 2014, 104, .	1.5	18
87	Monolayer FePt nanocrystal self-assembly embedded into atomic-layer-deposited Al2O3 films for nonvolatile memory applications. Journal of Alloys and Compounds, 2014, 588, 103-107.	2.8	8
88	Mechanical switching of ferroelectric polarization in ultrathin BaTiO3 films: The effects of epitaxial strain. Applied Physics Letters, 2014, 104, .	1.5	45
89	Effective anomalous Hall coefficient in an ultrathin Co layer sandwiched by Pt layers. Journal of Applied Physics, 2014, 115, .	1.1	8
90	Ferroelectric modulation on resonant tunneling through perovskite double-barriers. Applied Physics Letters, 2014, 104, .	1.5	9

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91	Effects of Î³-ray irradiation on ferroelectric properties of Pr and Mn co-substituted BiFeO₃ thin films. Journal Physics D: Applied Physics, 2014, 47, 045310.	1.3	8
92	Memristive behaviors in Pt/BaTiO3/Nb:SrTiO3 ferroelectric tunnel junctions. Applied Physics Letters, 2014, 105, .	1.5	47
93	Rectifying characteristics of a Fe:SrTiO 3 /Nb:SrTiO 3 homojunction. Superlattices and Microstructures, 2014, 75, 72-78.	1.4	1
94	Resistive switching in $$hbox {BiFeO}_3$$ BiFeO 3 -based heterostructures due to ferroelectric modulation on interface Schottky barriers. Journal of Materials Science: Materials in Electronics, 2014, 25, 3251-3256.	1.1	13
95	Mesoscale Imperfections in MoS2 Atomic Layers Grown by a Vapor Transport Technique. Nano Letters, 2014, 14, 4682-4686.	4.5	67
96	Tiâ€“Alâ€“O nanocrystal charge trapping memory cells fabricated by atomic layer deposition. Thin Solid Films, 2014, 563, 6-9.	0.8	4
97	Nonvolatile memory capacitors based on Al2O3 tunneling and HfO2 blocking layers with charge storage in atomic-layer-deposited Pt nanocrystals. Applied Surface Science, 2014, 289, 332-337.	3.1	19
98	Strain effects on transport and magnetic properties of Pr0.65La0.05Ca0.3MnO3 thin films. Physica B: Condensed Matter, 2014, 434, 106-111.	1.3	2
99	Ultrathin ZnO coating for improved electrochemical performance of LiNi0.5Co0.2Mn0.3O2 cathode material. Journal of Power Sources, 2014, 266, 433-439.	4.0	212
100	Recent advances in spin transport in organic semiconductors. Science China: Physics, Mechanics and Astronomy, 2013, 56, 142-150.	2.0	13
101	Temperature-dependent tunneling electroresistance in Pt/BaTiO3/SrRuO3 ferroelectric tunnel junctions. Applied Physics Letters, 2013, 103, .	1.5	31
102	Ferroelectric-field-effect-enhanced electroresistance in metal/ferroelectric/semiconductor tunnel junctions. Nature Materials, 2013, 12, 617-621.	13.3	554
103	Bipolar resistive switching based on SrTiO3/YBa2Cu3O7epi-layers. Journal Physics D: Applied Physics, 2013, 46, 035308.	1.3	10
104	Bipolar resistive switching in BiFe 0.95 Zn 0.05 O 3 films. Chinese Physics B, 2013, 22, 107702.	0.7	8
105	The metallic interface between insulating NdGaO₃ and SrTiO₃ perovskites. Applied Physics Letters, 2013, 103, 201602.	1.5	25
106	Tuning the polarization state of light via time retardation with a microstructured surface. Physical Review B, 2013, 88, .	1.1	22
107	Spectroscopy of self-assembled one-dimensional atomic string: The role of step edge. Applied Physics Letters, 2013, 103, 081608.	1.5	3
108	Positron annihilation studies on the behaviour of vacancies in LaAlO₃/SrTiO₃ heterostructures. Journal Physics D: Applied Physics, 2012, 45, 445305.	1.3	9

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109	Strain effects on magnetic characteristics of ultrathin La0.7Sr0.3MnO3in epitaxial La0.7Sr0.3MnO3/BaTiO3superlattices. Journal of Applied Physics, 2012, 112, 123919.	1.1	14
110	Enhanced Magnetoelectric Response and Phonon Abnormality of Self-assembled Feather-like CoFe2O4-BaTiO3 Nanostructures. Materials Research Society Symposia Proceedings, 2012, 1454, 57-62.	0.1	0
111	Electron mobility determination of efficient phosphorescent iridium complexes with tetraphenylimidodiphosphinate ligand via transient electroluminescence method. Applied Physics Letters, 2012, 100, 073303.	1.5	40
112	Mechanism of Polarization Fatigue in BiFeO₃. ACS Nano, 2012, 6, 8997-9004.	7.3	71
113	Magnetic Ordering and Structural Phase Transitions in a Strained Ultrathin<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>SrRuO</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:mo>/</mml:mo><mml:msub><mml Physical Review Letters, 2012, 109, 157003.	2.9	51
114	HfxZr1â^'xO2 films chemical vapor deposited from a single source precursor of anhydrous HfxZr1â^'x(NO3)4. Journal of Crystal Growth, 2012, 346, 12-16.	0.7	2
115	Magnetic and transport characteristics of long-period [(LaMnO3)n/(SrMnO3)n]m (nâ€‰â‰¥â€‰3) superlattices. Journal of Applied Physics, 2012, 112, 103917.	1.1	2
116	Characteristics of Gd2â^'xLaxO3 high-k films by metal-organic chemical vapor deposition. Microelectronic Engineering, 2012, 94, 38-43.	1.1	4
117	Polarization fatigue of Pr and Mn co-substituted BiFeO3 thin films. Applied Physics Letters, 2011, 99, .	1.5	32
118	Currentâ€“voltage characteristics of solâ€“gel derived SrZrO3 thin films for resistive memory applications. Journal of Alloys and Compounds, 2011, 509, 2050-2053.	2.8	17
119	Multiferroic properties of (Bi1â^'xPrx)(Fe0.95Mn0.05)O3 thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2011, 176, 990-995.	1.7	30
120	Effects of Pr Substitution on Electrical Properties of Bi(Fe0.95Mn0.05)O3Thin Films. Japanese Journal of Applied Physics, 2011, 50, 01BF07.	0.8	1
121	Photovoltaic property of BiFeO3 thin films with 109Â° domains. Applied Physics Letters, 2011, 99, .	1.5	56
122	Fabrication and characterization of La-doped HfO2 gate dielectrics by metal-organic chemical vapor deposition. Applied Surface Science, 2010, 256, 2496-2499.	3.1	35
123	The roles of B-site ions in lead strontium zirconate titanate thin films for electrically tunable device applications. Thin Solid Films, 2010, 518, 3929-3932.	0.8	1
124	Enhanced ferromagnetism at the rhombohedralâ€“tetragonal phase boundary in Pr and Mn co-substituted powders. Solid State Communications, 2010, 150, 2081-2084.	0.9	48
125	Temperature-dependent leakage current characteristics of Pr and Mn cosubstituted BiFeO3 thin films. Applied Physics Letters, 2010, 96, 202904.	1.5	26
126	Polarization switching in quasiplanar BiFeO3 capacitors. Applied Physics Letters, 2010, 97, .	1.5	26

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127	Impact of the Al/Hf ratio on the electrical properties and band alignments of atomic-layer-deposited HfO₂/Al₂O₃on S-passivated GaAs substrates. Semiconductor Science and Technology, 2010, 25, 055012.	1.0	15
128	Composition-dependent electrical characteristics and interface microstructures of solution-derived Nd-substituted Bi₄Ti₃O₁₂thin films on Pt electrodes. Journal Physics D: Applied Physics, 2009, 42, 185412.	1.3	3
129	Preparation of (1â^'x%)(Na0.5Bi0.5)TiO3â€“x%SrTiO3 thin films by a solâ€“gel method for dielectric tunable applications. Journal of Sol-Gel Science and Technology, 2009, 49, 29-34.	1.1	28
130	Synthesis, structure and physical properties of the one-dimensional chain complex of tetrathiafulvalene carboxylate. Science in China Series B: Chemistry, 2009, 52, 1596-1601.	0.8	15
131	Microstructures and impedance studies of Bi3.15Nd0.85Ti3O12 thin films. Applied Physics A: Materials Science and Processing, 2009, 95, 517-521.	1.1	6
132	Structural phase transition due to La substitution in Bi₄Ti₃O₁₂. Phase Transitions, 2009, 82, 146-155.	0.6	9
133	Effect of Forming Gas on Properties of SrBi₂Ta₂O₉ Ferroelectric Thin Film and Powder. Wuji Cailiao Xuebao/Journal of Inorganic Materials, 2009, 24, 737-740.	0.6	5
134	Preparation and characterization of Pb0.56Sr0.44Zr0.52Ti0.48O3 inverse opal. Journal of Sol-Gel Science and Technology, 2008, 45, 315-318.	1.1	2
135	Ferroelectric properties of bilayer structured Pb(Zr0.52Ti0.48)O3/SrBi2Ta2O9 (PZT/SBT) thin films on Pt/TiO2/SiO2/Si substrates. Applied Surface Science, 2008, 254, 1583-1586.	3.1	13
136	Transmission Electron Microscopy Observations on the Interfacial Structures of the Pt/SrBi2Ta2O9/Pt Thin-Film Capacitors Prepared by Metallo-Organic Decomposition. Journal of the American Ceramic Society, 2008, 91, 979-985.	1.9	0
137	CHEMICAL VAPOR DEPOSITION OF Zr_xHf_{1-x}O₂ THIN FILMS USING ANHYDROUS MIXED-METAL NITRATES PRECURSORS. Integrated Ferroelectrics, 2008, 97, 93-102.	0.3	2
138	Polarization offset of homogeneous Bi3.15Nd0.85Ti3O12 ferroelectric thin films. Journal of Applied Physics, 2008, 104, .	1.1	2
139	Polarization offsets of compositionally graded Nd-substituted Bi4Ti3O12 ferroelectric thin films. Applied Physics Letters, 2008, 93, 062904.	1.5	6
140	Fatigue characteristics of Nd-substituted Bi₄Ti₃O₁₂ferroelectric thin films at elevated temperatures. Journal Physics D: Applied Physics, 2008, 41, 122003.	1.3	7
141	Low-temperature electrical characteristics of Bi3.15Nd0.85Ti3O12 thin films. Applied Physics Letters, 2007, 90, 062902.	1.5	12
142	Effects of processing on all-optical poling characteristics of guest-host azo-dye polymer thin films. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 1114-1122.	0.8	6
143	Giant magnetoresistance in transition-metal-doped ZnO films. Applied Physics Letters, 2006, 88, 252110.	1.5	39
144	Sequence of Events for the Formation of Titanate Nanotubes, Nanofibers, Nanowires, and Nanobelts. Chemistry of Materials, 2006, 18, 547-553.	3.2	247

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145	Optical properties of (Mn, Co) co-doped ZnO films prepared by dual-radio frequency magnetron sputtering. Thin Solid Films, 2006, 515, 2361-2365.	0.8	28
146	Bell-mouthed single-crystalline tubular ZnO prepared by a soft solution method. Materials Chemistry and Physics, 2006, 96, 51-54.	2.0	9
147	Chemical Vapor Deposition of ZrxTi1-xO and HfxTi1-xO Thin Films Using the Composite Anhydrous Nitrate Precursors. Materials Research Society Symposia Proceedings, 2006, 917, 1.	0.1	0
148	Effects of the substitution of Pb for Ba in (Ba,Sr)TiO3 films on the temperature stability of the tunable properties. Applied Physics Letters, 2006, 88, 182909.	1.5	24
149	Strontium-modified lead zirconate titanate thin films for electrically tunable device applications. Journal of Applied Physics, 2006, 100, 036102.	1.1	16
150	STRUCTURE AND PROPERTIES OF BARIUM STRONTIUM TITANATE NANOPARTICLES SYNTHESIZED BY A HYDROTHERMAL METHOD. Integrated Ferroelectrics, 2006, 78, 289-297.	0.3	2
151	Effects of applied electric field during postannealing on the tunable properties of (Ba,Sr)TiO3 thin films. Applied Physics Letters, 2005, 87, 052902.	1.5	9
152	Leakage current characteristics of Ptâˆ•Bi3.25La0.75Ti3O12âˆ•Pt thin-film capacitors. Journal of Applied Physics, 2005, 97, 106110.	1.1	16
153	Magnetic and transport properties of (Mn, Co)-codoped ZnO films prepared by radio-frequency magnetron cosputtering. Journal of Applied Physics, 2005, 98, 053908.	1.1	60
154	SYNTHESIS AND CHARACTERIZATION OF FERROELECTRIC NANOCRYSTAL POWDERS OF SrBi2Ta2O9 BY A POLYMERIZABLE COMPLEX METHOD. International Journal of Modern Physics B, 2005, 19, 2514-2519.	1.0	3
155	Co-doped titanate nanotubes. Applied Physics Letters, 2005, 87, 112501.	1.5	59
156	Electrical properties of Bi3.25La0.75Ti3O12/LaAlO3/Si structures for ferroelectric field effect transistor applications. Journal Physics D: Applied Physics, 2004, 37, 832-835.	1.3	3
157	Dielectric characterization of Bi3.25La0.75Ti3O12 thin films. Applied Physics Letters, 2004, 84, 4505-4507.	1.5	65
158	Structure and electrical properties of Bi3.15Nd0.85Ti3O12 ferroelectric thin films. Journal of Applied Physics, 2004, 95, 4275-4281.	1.1	55
159	Characteristics of SrBi2Ta2O9 ferroelectric films in an in situ applied low electric field prepared by metalorganic decomposition. Solid State Communications, 2003, 125, 469-473.	0.9	3
160	Role of interfacial diffusion in SrBi2Ta2O9 thin-film capacitors. Microelectronic Engineering, 2003, 66, 654-661.	1.1	7
161	Growth and characterization of Al2O3 gate dielectric films by low-pressure metalorganic chemical vapor deposition. Microelectronic Engineering, 2003, 66, 842-848.	1.1	19
162	Characteristics of metalâ€“ferroelectricâ€“insulatorâ€“semiconductor structure using La-modified Bi4Ti3O12 as the ferroelectric layer. Microelectronic Engineering, 2003, 66, 773-778.	1.1	12

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163	Characteristics of LaAlO3 gate dielectrics on Si grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2003, 83, 3540-3542.	1.5	61
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165	Effect of In-Situ Applied Electric Field on Structure and Ferroelectric Properties of SrBi 2 Ta 2 O 9 Films. Integrated Ferroelectrics, 2002, 47, 153-158.	0.3	1
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